LUXNET CORPORATION

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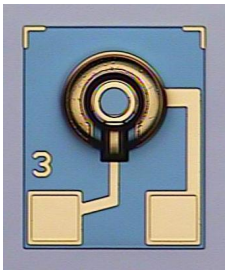
25 Gbps 850 nm PIN

L-CR-IM00-00

Part Number: L-CR-IM00-00
Applications: 25 Gbps

Absolute Maximum Ratings (T = 25°C):

Parameter	Symbol	Unit	Value
Forward Current	I_F	mA	10
Reverse Voltage	V_R	V	40
Reverse Current	I_R	mA	1
Operating Temperature	T_{op}	°C	0 - 90
Storage Temperature	T_{stg}	°C	-40 - 100



Electro-optical Characteristics (T = 25°C, unless noted otherwise):

Parameter	Symbol	Unit	Min.	Typ.	Max.	Test Condition
Aperture	D	μm		32		
Responsivity	R	A/W		0.5		V_R = 5 V λ = 850 nm
Dark Current	I_D	nA		0.1	1.0	V_R = 5 V
Breakdown Voltage	V_B	V	50			I_R = 1 μA
Capacitance	C	pF		0.07	0.1	V_R = 2 V f = 1 MHz
Peak Wavelength	λ	nm		850	860	
Cut-off Frequency	f_C	GHz		22		V_R = 2 V R_L = 50Ω

Chip configuration:

1. Both anode and cathode contacts on top (epi) surface.
2. Dimension: 250 um (width) x 300 um (length) x 130 um (thickness)
   Tolerance: +/-12.5um
3. Bond pad size: 60 x 60 um square
4. P-bond pad on left